Data Sheet

## April 12, 2005

# FN6093.2

# Ultra Low ON-Resistance, Low Voltage, Single Supply, Dual SPDT Analog Switch

intercil

The Intersil ISL43L220 device is a low ON-resistance, low voltage, bidirectional, dual single-pole/double-throw (SPDT) analog switch designed to operate from a single +1.1V to +4.5V supply. Targeted applications include battery powered equipment that benefit from low R<sub>ON</sub> (0.22 $\Omega$ ) and fast switching speeds (t<sub>ON</sub> = 11ns, t<sub>OFF</sub> = 5ns). The digital logic input is 1.8V logic-compatible when using a single +3V supply.

Cell phones, for example, often face ASIC functionality limitations. The number of analog input or GPIO pins may be limited and digital geometries are not well suited to analog switch performance. This part may be used to "mux-in" additional functionality while reducing ASIC design risk. The ISL43L220 is offered in a small form factor package, alleviating board space limitations.

The ISL43L220 is a committed dual single-pole/double-throw (SPDT) that consist of two normally open (NO) and two normally closed (NC) switches. This configuration can also be used as a dual 2-to-1 multiplexer. The ISL43L220 is pin compatible with the MAX4684 and MAX4685.

#### TABLE 1. FEATURES AT A GLANCE

	ISL43L220
Number of Switches	2
SW	SPDT or 2-1 MUX
4.3V R <sub>ON</sub>	0.22Ω
4.3V t <sub>ON</sub> /t <sub>OFF</sub>	11ns/5ns
3V R <sub>ON</sub>	0.26Ω
3V t <sub>ON</sub> /t <sub>OFF</sub>	14ns/6ns
1.8V R <sub>ON</sub>	0.5Ω
1.8V t <sub>ON</sub> /t <sub>OFF</sub>	20ns/8ns
Packages	10Ld 3x3 thin DFN

# Features

- Pb-Free Available as an Option (RoHS Compliant) (See Ordering Info)
- ON Resistance (R<sub>ON</sub>)

•	ON Resistance (RON)
	- V+ = +4.3V 0.22Ω
	- V+ = $+3.0V$ 0.26 $\Omega$
	- $V + = +1.8V$ $0.5\Omega$
•	$R_{\mbox{ON}}$ Matching Between Channels 0.03 $\!\Omega$
•	$R_{\mbox{ON}}$ Flatness Across Signal Range $\ldots \ldots \ldots \ldots 0.03 \Omega$
•	Single Supply Operation +1.1V to +4.5V
•	Low Power Consumption (PD)
•	Fast Switching Action (V+ = +4.3V)
	- t <sub>ON</sub> 11ns
	- t <sub>OFF</sub> 5ns
	Cuaranteed Brook Before Make

- Guaranteed Break-Before-Make
- 1.8V Logic Compatible (+3V supply)
- Available in 10 lead 3x3 thin DFN

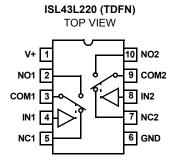
## Applications

- · Battery powered, handheld, and portable equipment
  - Cellular/mobile phones
  - Pagers
  - Laptops, notebooks, palmtops
- · Portable Test and Measurement
- · Medical Equipment
- Audio and video switching

## Related Literature

- Technical Brief TB363 "Guidelines for Handling and Processing Moisture Sensitive Surface Mount Devices (SMDs)"
- Application Note AN557 "Recommended Test Procedures for Analog Switches"

## Pinout (Note 1)



#### NOTE:

1. Switches Shown for Logic "0" Input.

# Truth Table

LOGIC	PIN NC	PIN NO
0	ON	OFF
1	OFF	ON

NOTE: Logic "0"  ${\leq}0.5V.$  Logic "1"  ${\geq}1.4V$  with a 3V supply.

# **Pin Descriptions**

PIN	FUNCTION			
V+	System Power Supply Input (+1.1V to +4.5V)			
GND	Ground Connection			
IN	Digital Control Input			
COM	Analog Switch Common Pin			
NO	Analog Switch Normally Open Pin			
NC	Analog Switch Normally Closed Pin			

# **Ordering Information**

PART NO. (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
ISL43L220IR (220)	-40 to 85	10 Ld 3x3 thin DFN	L10.3x3A
ISL43L220IR-T (L20)	-40 to 85	10 Ld 3x3 thin DFN Tape and Reel	L10.3x3A
ISL43L220IRZ (220) (See Note)	-40 to 85	10 Ld 3x3 thin DFN (Pb-free)	L10.3x3A
ISL43L220IRZ-T (L20) (See Note)	-40 to 85	10 Ld 3x3 thin DFN Tape and Reel (Pb-free)	L10.3x3A

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

#### **Absolute Maximum Ratings**

V+ to GND
Input Voltages
NO, NC, IN (Note 2)
Output Voltages
COM (Note 2)
Continuous Current NO, NC, or COM ±300mA
Peak Current NO, NC, or COM
(Pulsed 1ms, 10% Duty Cycle, Max) ±500mA
ESD Rating:
HBM
MM
CDM>1kV

**Electrical Specifications - 4.3V Supply** 

#### **Thermal Information**

Thermal Resistance (Typical, Note 3)	θ <sub>JA</sub> (°C/W)
10 Ld 3x3 DFN Package	110
Maximum Junction Temperature (Plastic Package)	
Maximum Storage Temperature Range65	5°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(Lead Tips Only)	

## **Operating Conditions**

Test Conditions: V+ = +3.9V to +4.5V, GND = 0V,  $V_{INH}$  = 1.6V,  $V_{INL}$  = 0.5V (Notes 4, 6),

Temperature Range	
ISL43L220IR	-40°C to 85°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTES:

2. Signals on NC, NO, IN, or COM exceeding V+ or GND are clamped by internal diodes. Limit forward diode current to maximum current ratings.

3.  $\theta_{JA}$  is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	STICS		++			
Analog Signal Range, V <sub>ANALOG</sub>		Full	0	-	V+	V
ON Resistance, R <sub>ON</sub>	V+ = 3.9V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = 0V to V+	25	-	0.23	0.35	Ω
	(See Figure 5)	Full	-	-	0.35	Ω
R <sub>ON</sub> Matching Between Channels,	V+ = 3.9V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = Voltage at	25	-	0.03	0.06	Ω
ΔR <sub>ON</sub>	max R <sub>ON</sub> (Note 9)	Full	-	-	0.06	Ω
R <sub>ON</sub> Flatness, R <sub>FLAT(ON)</sub>	V+ = 3.9V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = 0V to V+	25	-	0.03	0.08	Ω
	(Note 7)	Full	-	-	0.08	Ω
NO or NC OFF Leakage Current,	V+ = 4.5V, V <sub>COM</sub> = 0.3V, 3V, V <sub>NO</sub> or V <sub>NC</sub> = 3V, 0.3V	25	-45	-	45	nA
INO(OFF) or INC(OFF)		Full	-110	-	110	nA
COM ON Leakage Current,	or Floating	25	-45	-	45	nA
ICOM(ON)		Full	-100	-	100	nA
DYNAMIC CHARACTERISTICS						
Turn-ON Time, t <sub>ON</sub>	$V_{+} = 3.9V, V_{NO} \text{ or } V_{NC} = 1.5V, R_{L} = 50\Omega, C_{L} = 35pF$	25	-	12	17 ns	
	(See Figure 1, Note 8)	Full	-	-	22	ns
Turn-OFF Time, t <sub>OFF</sub>	$V_{+} = 3.9V, V_{NO} \text{ or } V_{NC} = 1.5V, R_{L} = 50\Omega, C_{L} = 35pF$	25	-	5	10	ns
	(See Figure 1, Note 8)	Full	-	-	15	ns
Break-Before-Make Time Delay, $t_D$	V+ = 4.5V, V <sub>NO</sub> or V <sub>NC</sub> = 1.5V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 3, Note 8)	Full	2	4	-	ns
Charge Injection, Q	$C_L$ = 1.0nF, $V_G$ = 0V, $R_G$ = 0 $\Omega$ , (See Figure 2)	25	-	128	-	pC
OFF Isolation	$R_L$ = 50 $\Omega$ , $C_L$ = 5pF, f = 100kHz, $V_{COM}$ = 1 $V_{RMS}$ (See Figure 4)	25	-	68	-	dB
Crosstalk (Channel-to-Channel)	$R_L$ = 50 $\Omega$ , $C_L$ = 5pF, f = 100kHz, $V_{COM}$ = 1 $V_{RMS}$ , (See Figure 6)	25	-	-95	-	dB
Total Harmonic Distortion	f = 20Hz to 20kHz, $V_{COM}$ = 2 $V_{P-P}$ , $R_L$ = 600 $\Omega$	25	-	0.003	-	%
NO or NC OFF Capacitance, COFF	f = 1MHz, $V_{NO}$ or $V_{NC}$ = $V_{COM}$ = 0V (See Figure 7)	25	-	115	-	pF
COM ON Capacitance, C <sub>COM(ON)</sub>	f = 1MHz, $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ (See Figure 7)	25	-	224	-	pF

### **Electrical Specifications - 4.3V Supply**

Test Conditions: V+ = +3.9V to +4.5V, GND = 0V,  $V_{INH}$  = 1.6V,  $V_{INL}$  = 0.5V (Notes 4, 6), Unless Otherwise Specified **(Continued)** 

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
POWER SUPPLY CHARACTERIS	TICS	÷				÷
Power Supply Range		Full	1.1	-	4.5	V
Positive Supply Current, I+	V+ =1.1V to 4.5V, V <sub>IN</sub> = 0V or V+	25	-	-	0.06	μA
		Full	-	-	1	μA
DIGITAL INPUT CHARACTERISTI	cs	ŧ			•	
Input Voltage Low, VINL		Full	-	-	0.5	V
Input Voltage High, V <sub>INH</sub>		Full	1.6	-	-	V
Input Current, I <sub>INH</sub> , I <sub>INL</sub>	V+ = 4.5V, V <sub>IN</sub> = 0V or V+ (Note 8)	Full	-0.5	-	0.5	μA

NOTES:

- 4.  $V_{IN}$  = input voltage to perform proper function.
- 5. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- 6. Parts are 100% tested at +25°C. Limits across the full temperature range are guaranteed by design and correlation.
- 7. Flatness is defined as the difference between maximum and minimum value of on-resistance over the specified analog signal range.
- 8. Guaranteed but not tested.
- 9. R<sub>ON</sub> matching between channels is calculated by subtracting the channel with the highest max Ron value from the channel with lowest max Ron value, between NC1 and NC2 or between NO1 and NO2.

## **Electrical Specifications - 3V Supply**

Test Conditions: V+ = +2.7V to +3.3V, GND = 0V, V<sub>INH</sub> = 1.4V, V<sub>INL</sub> = 0.5V (Notes 4, 6), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	STICS					• •
Analog Signal Range, V <sub>ANALOG</sub>		Full	0	-	V+	V
ON Resistance, R <sub>ON</sub>	V+ = 2.7V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = 0V to V+	25	-	0.29	0.4	Ω
	(See Figure 5, Note 8)	Full	-	-	0.4	Ω
R <sub>ON</sub> Matching Between Channels,	V+ = 2.7V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = Voltage at max	25	-	0.03	0.06	Ω
ΔR <sub>ON</sub>	R <sub>ON</sub> (Notes 8, 9)	Full	-	-	0.06	Ω
R <sub>ON</sub> Flatness, R <sub>FLAT(ON)</sub>	V+ = 2.7V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = 0V to V+	25	-	0.03	0.1	Ω
	(Notes 7, 8)	Full	-	-	0.1	Ω
NO or NC OFF Leakage Current,	V+ = 3.3V, V <sub>COM</sub> = 0.3V, 3V, V <sub>NO</sub> or V <sub>NC</sub> = 3V, 0.3V	25	-	1.1	-	nA
NO(OFF) or INC(OFF)	Full	-	25	-	nA	
COM ON Leakage Current,	$V_{+}$ = 3.3V, $V_{COM}$ = 0.3V, 3V, or $V_{NO}$ or $V_{NC}$ = 0.3V, 3V,	25	-	1.7	-	nA
COM(ON)	or Floating	Full	-	48	-	nA
DYNAMIC CHARACTERISTICS						r
Turn-ON Time, t <sub>ON</sub>	V+ = 2.7V, V <sub>NO</sub> or V <sub>NC</sub> = 1.5V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF	25	-	14	20	ns
	(See Figure 1, Note 8)	Full	-	-	25	ns
Turn-OFF Time, t <sub>OFF</sub>	V+ = 2.7V, V <sub>NO</sub> or V <sub>NC</sub> = 1.5V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF	25	-	6	12	ns
	(See Figure 1, Note 8)	Full	-	-	17	ns
Break-Before-Make Time Delay, $t_D$	V+ = 3.3V, V <sub>NO</sub> or V <sub>NC</sub> = 1.5V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 3, Note 8)	Full	2	7	-	ns
Charge Injection, Q	$C_L$ = 1.0nF, $V_G$ = 0V, $R_G$ = 0 $\Omega$ (See Figure 2)	25	-	95	-	рС

## **Electrical Specifications - 3V Supply**

Test Conditions: V+ = +2.7V to +3.3V, GND = 0V, V<sub>INH</sub> = 1.4V, V<sub>INL</sub> = 0.5V (Notes 4, 6), Unless Otherwise Specified (Continued)

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
OFF Isolation	$R_L = 50\Omega$ , $C_L = 5pF$ , f = 100kHz, $V_{COM} = 1V_{RMS}$ (See Figure 4)	25	-	68	-	dB
Crosstalk (Channel-to-Channel)	$R_L = 50\Omega$ , $C_L = 5pF$ , f = 100kHz, $V_{COM} = 1V_{RMS}$ (See Figure 6)	25	-	-95	-	dB
Total Harmonic Distortion	f = 20Hz to 20kHz, $V_{COM}$ = 2 $V_{P-P}$ , $R_L$ = 600 $\Omega$	25	-	0.003	-	%
NO or NC OFF Capacitance, COFF	f = 1MHz, $V_{NO}$ or $V_{NC}$ = $V_{COM}$ = 0V (See Figure 7)	25	-	115	-	pF
COM ON Capacitance, C <sub>COM(ON)</sub>	f = 1MHz, $V_{NO}$ or $V_{NC}$ = $V_{COM}$ = 0V (See Figure 7)	25	-	224	-	pF
POWER SUPPLY CHARACTERIST	ics	1	11			P.
Power Supply Range		Full	1.1	-	4.5	V
Positive Supply Current, I+	V+ =1.1V to 3.6V, V <sub>IN</sub> = 0V or V+	25	-	0.014	-	μA
		Full	-	0.52	-	μA
DIGITAL INPUT CHARACTERISTIC	SS	- <b>I</b>	11			1
Input Voltage Low, V <sub>INL</sub>		Full	-	-	0.5	V
Input Voltage High, VINH		Full	1.4	-	-	V
Input Current, I <sub>INH</sub> , I <sub>INL</sub>	V+ = 3.3V, V <sub>IN</sub> = 0V or V+ (Note 8)	Full	-0.5	-	0.5	μA

**Electrical Specifications - 1.8V Supply** 

Test Conditions: V+ = +1.65V to +2V, GND = 0V, V\_{INH} = 1.0V, V\_{INL} = 0.4V (Notes 4, 6), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS		(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	TICS					
Analog Signal Range, V <sub>ANALOG</sub>		Full	0	-	V+	V
ON Resistance, R <sub>ON</sub>	V+ = 1.65V, I <sub>COM</sub> = 100mA, V <sub>NO</sub> or V <sub>NC</sub> = 0V to V+, (See Figure 5, Note 8)	25	-	0.5	0.8	Ω
		Full	-	-	0.8	Ω
NO or NC OFF Leakage Current, INO(OFF) or INC(OFF)	V+ = 2.0V, $V_{COM}$ = 0.3V, 1.8V, $V_{NO}$ or $V_{NC}$ = 1.8V, 0.3V	25	-	1.1	-	nA
			-	25	-	nA
COM ON Leakage Current, ICOM(ON)	V+ = 2.0V, V <sub>COM</sub> = 0.3V, 1.8V, or V <sub>NO</sub> or V <sub>NC</sub> = 0.3V, 1.8V, or Floating	25	-	1.7	-	nA
		Full	-	48	-	nA
DYNAMIC CHARACTERISTICS						
Turn-ON Time, t <sub>ON</sub>	V+ = 1.65V, V <sub>NO</sub> or V <sub>NC</sub> = 1.0V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 1, Note 8)	25	-	22	28	ns
		Full	-	-	33	ns
Turn-OFF Time, t <sub>OFF</sub>	V+ = 1.65V, V <sub>NO</sub> or V <sub>NC</sub> = 1.0V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 1, Note 8)	25	-	9	15	ns
		Full	-	-	20	ns
Break-Before-Make Time Delay, t <sub>D</sub>	V+ = 2.0V, V <sub>NO</sub> or V <sub>NC</sub> = 1.0V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 3, Note 8)		2	9	-	ns
Charge Injection, Q	$C_L$ = 1.0nF, $V_G$ = 0V, $R_G$ = 0 $\Omega$ (See Figure 2)		-	49	-	рС
OFF Isolation	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5pF, f = 100kHz, V <sub>COM</sub> = 1V <sub>RMS</sub> (See Figure 4)		-	68	-	dB
Crosstalk (Channel-to-Channel)	$R_L$ = 50 $\Omega$ , $C_L$ = 5pF, f = 100kHz, $V_{COM}$ = 1 $V_{RMS}$ (See Figure 6)		-	-95	-	dB
NO or NC OFF Capacitance, COFF	f = 1MHz, $V_{NO}$ or $V_{NC}$ = $V_{COM}$ = 0V (See Figure 7)	25	-	115	-	pF
COM ON Capacitance, C <sub>COM(ON)</sub>	f = 1MHz, V <sub>NO</sub> or V <sub>NC</sub> = V <sub>COM</sub> = 0V (See Figure 7)		-	224	-	pF

### **Electrical Specifications - 1.8V Supply**

Test Conditions: V+ = +1.65V to +2V, GND = 0V,  $V_{INH}$  = 1.0V,  $V_{INL}$  = 0.4V (Notes 4, 6), Unless Otherwise Specified (Continued)

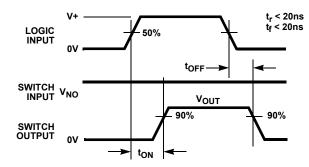
PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS	
DIGITAL INPUT CHARACTERISTICS							
Input Voltage Low, VINL		Full	-	-	0.4	V	
Input Voltage High, VINH		Full	1.0	-	-	V	
Input Current, I <sub>INH</sub> , I <sub>INL</sub>	V+ = 2.0V, V <sub>IN</sub> = 0V or V+ (Note 8)	Full	-0.5	-	0.5	μA	

#### **Electrical Specifications - 1.1V Supply**

Test Conditions: V+ = +1.1V, GND = 0V, V<sub>INH</sub> = 1.0V, V<sub>INL</sub> = 0.3V (Note 4), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS		(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	STICS					
Analog Signal Range, V <sub>ANALOG</sub>		Full	0	-	V+	V
ON Resistance, R <sub>ON</sub>	V+ = 1.1V, $I_{COM}$ = 100mA, $V_{NO}$ or $V_{NC}$ = 0V to V+, (See Figure 5)	25	-	2.6	3	Ω
		Full	-	3.4	4	Ω
DYNAMIC CHARACTERISTICS						
Turn-ON Time, t <sub>ON</sub>	V+ = 1.1V, V <sub>NO</sub> or V <sub>NC</sub> = 1.0V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 1, Note 8)	25	-	30	-	ns
		Full	-	35	-	ns
Turn-OFF Time, t <sub>OFF</sub>	V+ = 1.1V, V <sub>NO</sub> or V <sub>NC</sub> = 1.0V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 1, Note 8)	25	-	15	-	ns
		Full	-	20	-	ns
Break-Before-Make Time Delay, t <sub>D</sub>	V+ = 1.1V, V <sub>NO</sub> or V <sub>NC</sub> = 1.0V, R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 35pF (See Figure 3, Note 8)		-	4	-	ns
DIGITAL INPUT CHARACTERISTI	CS					
Input Voltage Low, V <sub>INL</sub>			-	0.3	-	V
Input Voltage High, V <sub>INH</sub>		Full	-	0.6	-	V
Input Current, I <sub>INH</sub> , I <sub>INL</sub>	V+ = 1.1V, V <sub>IN</sub> = 0V or V+ (Note 8)		-	0.5	-	μA

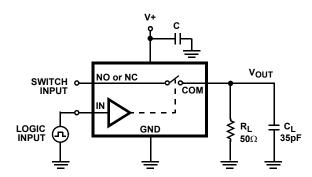
# Test Circuits and Waveforms



Logic input waveform is inverted for switches that have the opposite logic sense.

#### FIGURE 1A. MEASUREMENT POINTS

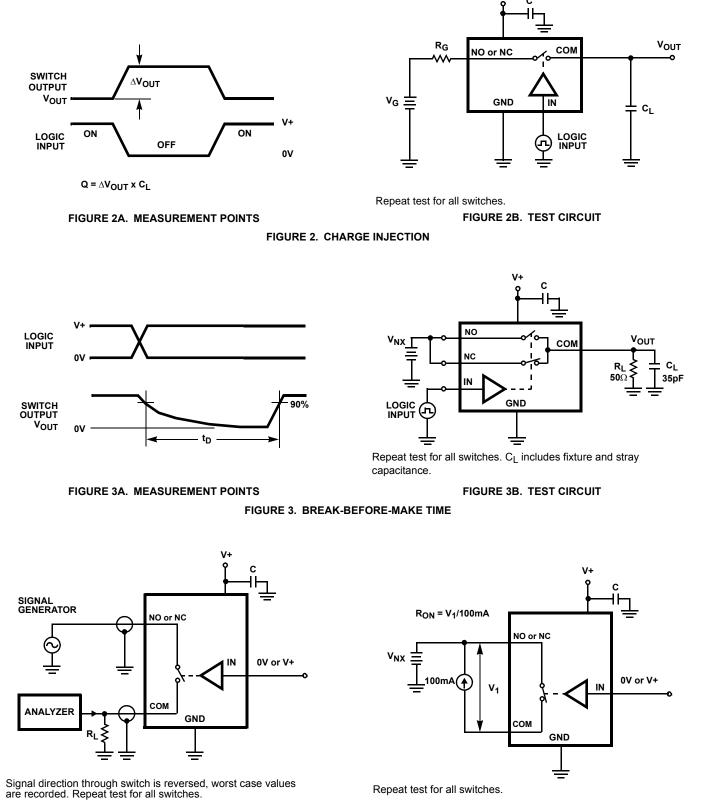
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Repeat test for all switches.  $C_L$  includes fixture and stray capacitance.  $R_L$ 

 $V_{OUT} = V_{(NO \text{ or } NC)} \frac{L}{R_{L} + R_{(ON)}}$ FIGURE 1B. TEST CIRCUIT

**FIGURE 1. SWITCHING TIMES** 



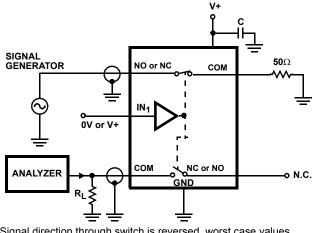
## Test Circuits and Waveforms (Continued)

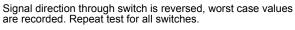
FIGURE 4. OFF ISOLATION TEST CIRCUIT

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#### FIGURE 5. RON TEST CIRCUIT

# Test Circuits and Waveforms (Continued)









The ISL43L220 is a bidirectional, dual single pole/double throw (SPDT) analog switch that offers precise switching capability from a single 1.1V to 4.5V supply with low on-resistance (0.22 $\Omega$ ) and high speed operation (t<sub>ON</sub> = 11ns, t<sub>OFF</sub> = 5ns). The device is especially well suited for portable battery powered equipment due to its low operating supply voltage (1.1V), low power consumption (4.5 $\mu$ W max), low leakage currents (110nA max), and the tiny DFN package. The ultra low on-resistance and Ron flatness provide very low insertion loss and distortion to applications that require signal reproduction.

## Supply Sequencing And Overvoltage Protection

With any CMOS device, proper power supply sequencing is required to protect the device from excessive input currents which might permanently damage the IC. All I/O pins contain ESD protection diodes from the pin to V+ and to GND (see Figure 8). To prevent forward biasing these diodes, V+ must be applied before any input signals, and the input signal voltages must remain between V+ and GND. If these conditions cannot be guaranteed, then one of the following two protection methods should be employed.

Logic inputs can easily be protected by adding a  $1k\Omega$  resistor in series with the input (see Figure 8). The resistor limits the input current below the threshold that produces permanent damage, and the sub-microamp input current produces an insignificant voltage drop during normal operation.

This method is not acceptable for the signal path inputs. Adding a series resistor to the switch input defeats the purpose of using a low  $R_{ON}$  switch, so two small signal diodes can be added in series with the supply pins to provide overvoltage protection for all pins (see Figure 8). These

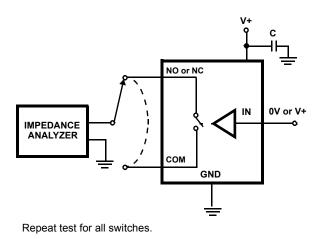


FIGURE 7. CAPACITANCE TEST CIRCUIT

additional diodes limit the analog signal from 1V below V+ to 1V above GND. The low leakage current performance is unaffected by this approach, but the switch signal range is reduced and the resistance may increase, especially at low supply voltages.

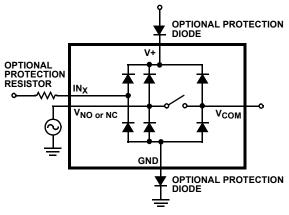


FIGURE 8. OVERVOLTAGE PROTECTION

# Power-Supply Considerations

The ISL43L220 construction is typical of most single supply CMOS analog switches, in that they have two supply pins: V+ and GND. V+ and GND drive the internal CMOS switches and set their analog voltage limits. Unlike switches with a 4V maximum supply voltage, the ISL43L220 4.7V maximum supply voltage provides plenty of room for the 10% tolerance of 4.3V supplies, as well as room for overshoot and noise spikes.

The minimum recommended supply voltage is 1.1V. It is important to note that the input signal range, switching times, and on-resistance degrade at lower supply voltages. Refer

to the electrical specification tables and *Typical Performance* curves for details.

V+ and GND also power the internal logic and level shifters. The level shifters convert the input logic levels to switched V+ and GND signals to drive the analog switch gate terminals.

This family of switches cannot be operated with bipolar supplies, because the input switching point becomes negative in this configuration.

#### Logic-Level Thresholds

This switch family is 1.8V CMOS compatible (0.5V and 1.4V) over a supply range of 2.0V to 3.6V (see Figure 16). At 3.6V the V<sub>IH</sub> level is about 1.27V. This is still below the 1.8V CMOS guaranteed high output minimum level of 1.4V, but noise margin is reduced.

The digital input stages draw supply current whenever the digital input voltage is not at one of the supply rails. Driving the digital input signals from GND to V+ with a fast transition time minimizes power dissipation.

#### **High-Frequency Performance**

In 50 $\Omega$  systems, the signal response is reasonably flat even past 30MHz with a -3dB bandwidth of 120MHz (see Figure 19). The frequency response is very consistent over a wide V+ range, and for varying analog signal levels.

An OFF switch acts like a capacitor and passes higher frequencies with less attenuation, resulting in signal

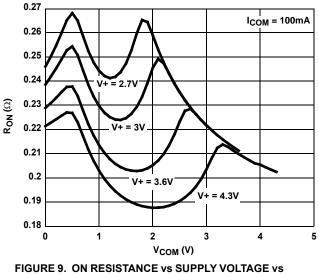
feedthrough from a switch's input to its output. Off Isolation is the resistance to this feedthrough, while Crosstalk indicates the amount of feedthrough from one switch to another. Figure 20 details the high Off Isolation and Crosstalk rejection provided by this part. At 100kHz, Off Isolation is about 68dB in 50 $\Omega$  systems, decreasing approximately 20dB per decade as frequency increases. Higher load impedances decrease Off Isolation and Crosstalk rejection due to the voltage divider action of the switch OFF impedance and the load impedance.

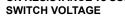
#### Leakage Considerations

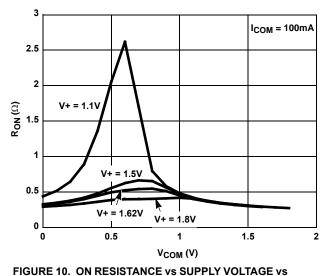
Reverse ESD protection diodes are internally connected between each analog-signal pin and both V+ and GND. One of these diodes conducts if any analog signal exceeds V+ or GND.

Virtually all the analog leakage current comes from the ESD diodes to V+ or GND. Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either V+ or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the V+ and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity. There is no connection between the analog signal paths and V+ or GND.









SWITCH VOLTAGE

# Typical Performance Curves T<sub>A</sub> = 25°C, Unless Otherwise Specified (Continued)

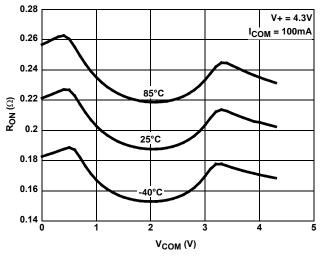


FIGURE 11. ON RESISTANCE vs SWITCH VOLTAGE

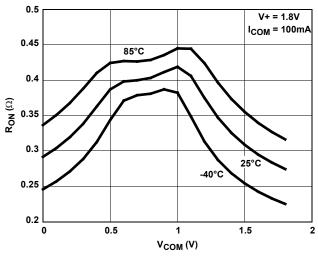


FIGURE 13. ON RESISTANCE vs SWITCH VOLTAGE

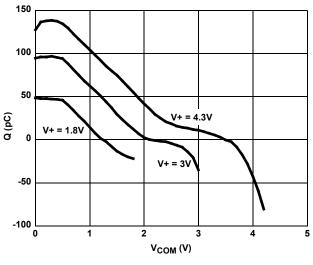


FIGURE 15. CHARGE INJECTION vs SWITCH VOLTAGE

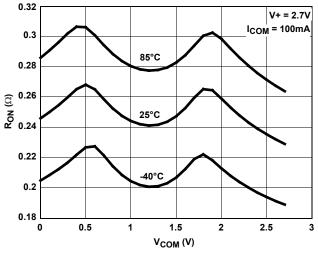
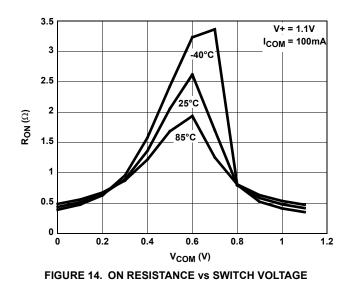


FIGURE 12. ON RESISTANCE vs SWITCH VOLTAGE



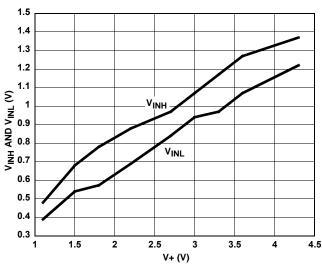


FIGURE 16. DIGITAL SWITCHING POINT vs SUPPLY VOLTAGE

Typical Performance Curves T<sub>A</sub> = 25°C, Unless Otherwise Specified (Continued)

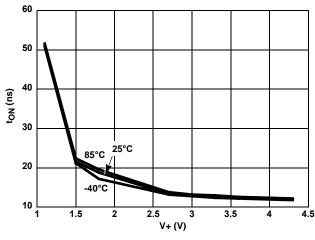
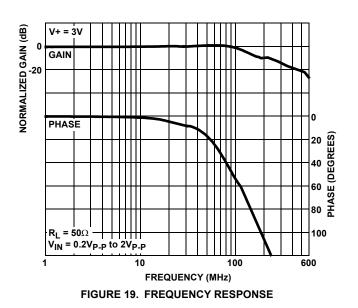
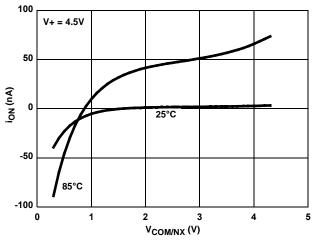


FIGURE 17. TURN - ON TIME vs SUPPLY VOLTAGE







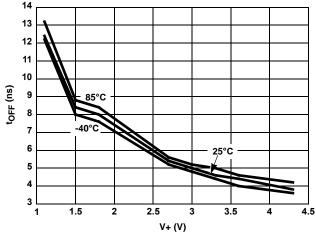
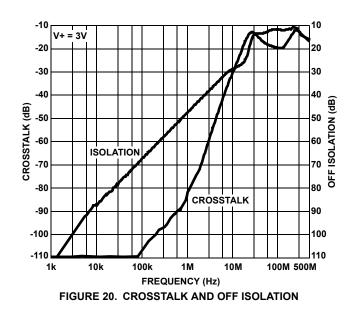
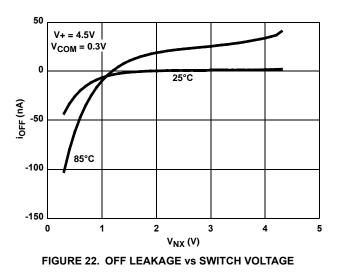


FIGURE 18. TURN - OFF TIME vs SUPPLY VOLTAGE





# **Die Characteristics**

## SUBSTRATE POTENTIAL (POWERED UP):

GND

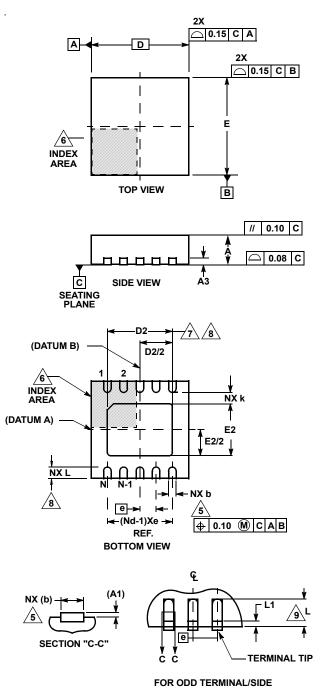
## TRANSISTOR COUNT:

114

## PROCESS:

Submicron CMOS

# Thin Dual Flat No-Lead Plastic Package (TDFN)



#### L10.3x3A

10 LEAD THIN DUAL FLAT NO-LEAD PLASTIC PACKAGE

SYMBOL	MIN	NOMINAL	MAX	NOTES	
А	0.70	0.75	0.80	-	
A1	-	-	0.05	-	
A3	0.20 REF			-	
b	0.20	0.25	0.30	5,8	
D		3.00 BSC			
D2	2.20	2.30	2.40	7,8	
E	3.00 BSC			-	
E2	1.40	1.50	1.60	7,8	
е	0.50 BSC			-	
k	0.25	-	-	-	
L	0.20	0.30	0.40	8	
L1	-	-	0.15	1	
N	10			2	
Nd	5			3	
				Rev. 1 6/04	

NOTES:

- 1. Dimensioning and tolerancing conform to ASME Y14.5-1994.
- 2. N is the number of terminals.
- 3. Nd refers to the number of terminals on D.
- 4. All dimensions are in millimeters. Angles are in degrees.
- 5. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
- 6. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.
- Dimensions D2 and E2 are for the exposed pads which provide improved electrical and thermal performance.
- 8. Nominal dimensions are provided to assist with PCB Land Pattern Design efforts, see Intersil Technical Brief TB389.
- Depending on the method of lead termination at the edge of the package, a maximum 0.15mm pull back (L1) maybe present. L minus L1 to be equal to or greater than 0.3mm.
- COMPLIANT TO JEDEC MO-229-WEED-3 except for dimensions E2 & D2.

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